

## BAX12, BAX12A

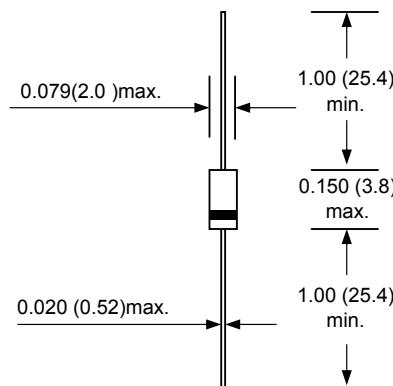
## CONTROLLED AVALANCHE DIODES

### FEATURES :

- \* Switching speed: max. 50 ns
- \* Continuous reverse voltage: max. 90V
- \* Repetitive peak reverse voltage: max. 90V
- \* Repetitive peak forward current: max. 800 mA
- \* Repetitive peak reverse current: max. 600mA
- \* Pb / RoHS Free

### MECHANICAL DATA :

- \* Case : DO-35 Glass Case
- \* Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- \* Polarity : Color band denotes cathode end
- \* Mounting position : Any
- \* Weight : 0.13 gram (approximately)



Dimensions in inches and ( millimeters )

### MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	90	V
Continuous Reverse Voltage	$V_R$	90	V
Continuous Forward Current	$I_F$	400	mA
Repetitive Peak Forward Current	$I_{FRM}$	800	A
Non-repetitive Peak Forward Current Square wave: $T_j = 25^\circ\text{C}$ prior to surge	$t = 1 \mu\text{s}$ $t = 100 \mu\text{s}$ $t = 10 \text{ ms}$	55 15 9	A
Total Power Dissipation , $T_a = 25^\circ\text{C}$	$P_{tot}$	450	mW
Repetitive Peak Reverse Current	$I_{RRM}$	600	mA
Junction Temperature	$T_j$	200	$^\circ\text{C}$
Storage Temperature Range	$T_s$	-65 to + 200	$^\circ\text{C}$

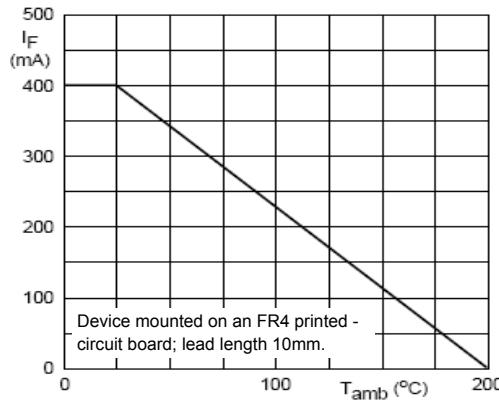
Note : (1) Device mounted on an FR4 printed circuit-board; lead length 10 mm.

### ELECTRICAL CHARACTERISTICS ( $T_j = 25^\circ\text{C}$ unless otherwise noted)

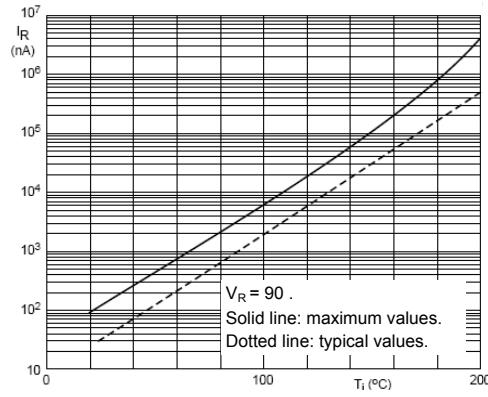
Parameter	Symbol	Test Condition	Min.	Max.	Unit
Reverse Avalanche Breakdown Voltage <b>BAX12</b>	$V_{(BR)R}$	$I_R = 1\text{mA}$ $I_R = 0.1\text{mA}$	120	170	V
Reverse Current	$I_R$	$V_R = 90 \text{ V}$ $V_R = 90 \text{ V}, T_j = 150^\circ\text{C}$	-	100	nA
Forward Voltage	$V_F$	$I_F = 400 \text{ mA}$	-	1.25	V
Diode Capacitance	Cd	$f = 1\text{MHz}; V_R = 0$	-	35	pF
Reverse Recovery Time	Tr	$I_F = 30\text{mA}, I_R = 30\text{mA}$ $R_L = 100 \Omega$ measured at $I_R = 3 \text{ mA}$	-	50	ns

## RATING AND CHARACTERISTIC CURVES ( BAX12, BAX12A )

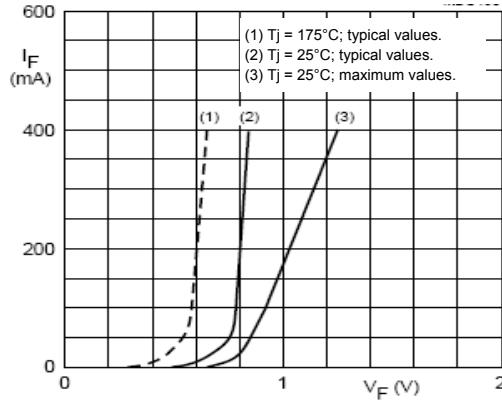
**Fig.1 - Maximum permissible continuous forward current as a function of ambient temperature.**



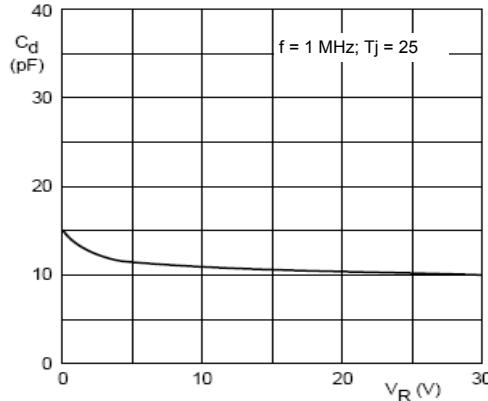
**Fig.3 - Reverse current as a function of junction temperature.**



**Fig.2 - Forward current as a function of forward voltage.**



**Fig.4 - Diode capacitance as a function of reverse voltage; typical values.**



**Fig.5 - Maximum permissible non-repetitive peak forward current as a function of pulse duration.**

